



BYV10EX-600P

Ultrafast power diode

25 September 2014

Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Enhanced avalanche energy capability

3. Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------|--|-----|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | - | 600 | V |
| $I_{F(AV)}$ | average forward current | $\delta = 0.5$; $T_h \leq 71$ °C; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 10 | A |
| Static characteristics | | | | | | |
| V_F | forward voltage | $I_F = 10$ A; $T_j = 150$ °C; Fig. 6 | - | - | 1.6 | V |
| Dynamic characteristics | | | | | | |
| t_{rr} | reverse recovery time | $I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 50$ A/ μ s; $T_j = 25$ °C; Fig. 7 | - | 35 | 50 | ns |
| Avalanche energy | | | | | | |
| E_{AS} | non-repetitive avalanche energy | $I_R = 2.6$ A; $T_{j(init)} = 25$ °C; $L = 15$ mH | - | 50 | - | mJ |

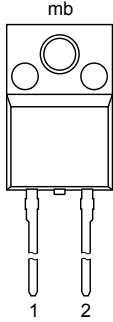



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|---|---|
| 1 | K | cathode |  <p style="text-align: center;">TO-220F (SOD113)</p> |  |
| 2 | A | anode | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

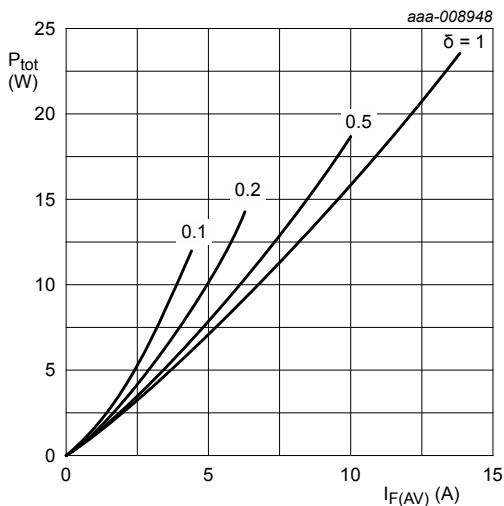
| Type number | Package | | |
|--------------|---------|---|---------|
| | Name | Description | Version |
| BYV10EX-600P | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack" | SOD113 |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

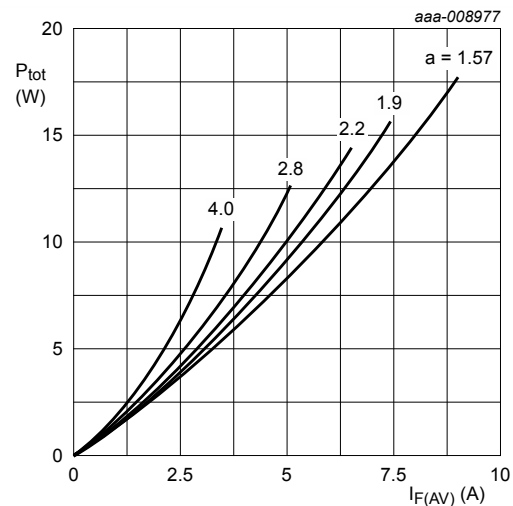
| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------|-------------------------------------|--|-----|-----|------------------|
| V_{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V_{RWM} | crest working reverse voltage | | - | 600 | V |
| V_R | reverse voltage | DC | - | 600 | V |
| $I_{F(AV)}$ | average forward current | $\delta = 0.5$; $T_h \leq 71^\circ\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 10 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_h \leq 71^\circ\text{C}$; square-wave pulse | - | 20 | A |
| I_{FSM} | non-repetitive peak forward current | $t_p = 10\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse; Fig. 4 | - | 75 | A |
| | | $t_p = 8.3\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse; Fig. 4 | - | 83 | A |
| T_{stg} | storage temperature | | -65 | 175 | $^\circ\text{C}$ |
| T_j | junction temperature | | - | 175 | $^\circ\text{C}$ |



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.268\ \text{V}; R_s = 0.031\ \Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 1.268\ \text{V}; R_s = 0.031\ \Omega$$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

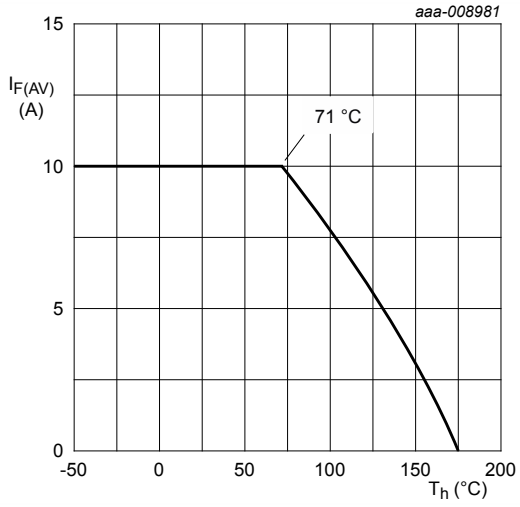


Fig. 3. Forward current as a function of heatsink temperature; maximum values

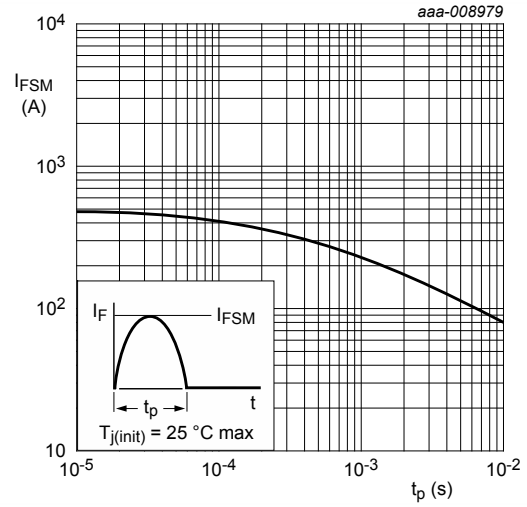


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|--|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | without heatsink compound | - | - | 7.2 | K/W |
| | | with heatsink compound; Fig. 5 | - | - | 5.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 55 | - | K/W |

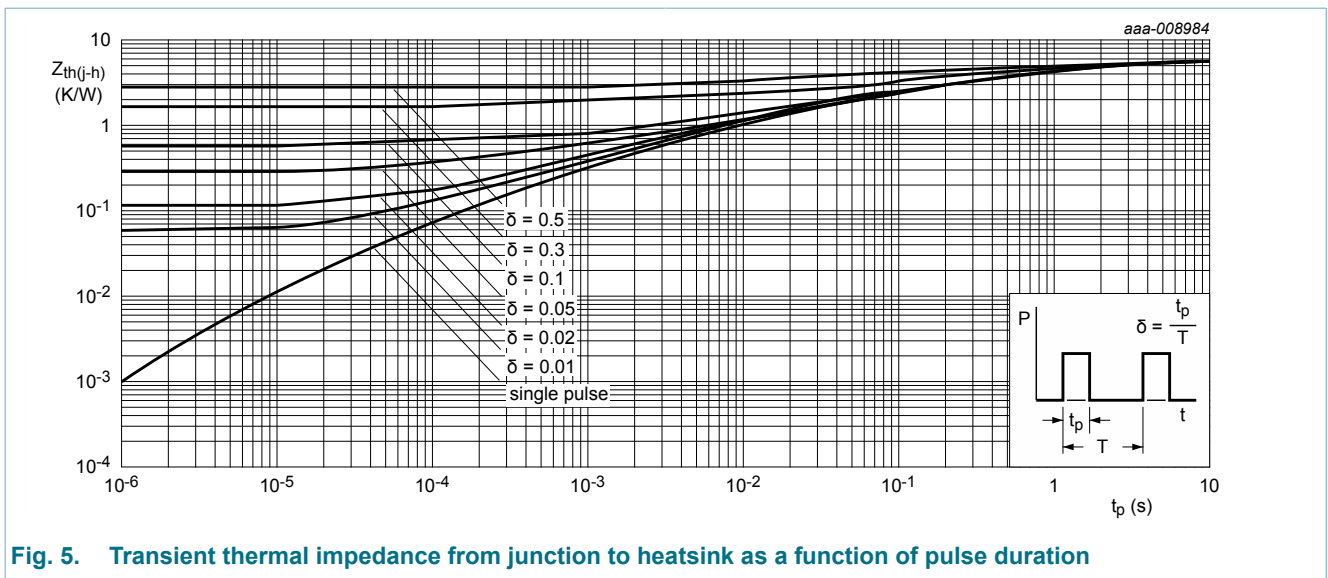


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

9. Isolation characteristics

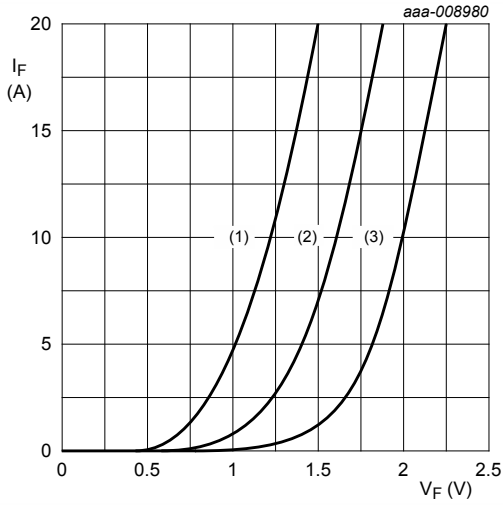
Table 6. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|---|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C_{isol} | isolation capacitance | f = 1 MHz; from cathode to external heatsink | - | 10 | - | pF |

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------|--|-----|------|-----|---------------|
| Static characteristics | | | | | | |
| V_F | forward voltage | $I_F = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 6 | - | 1.55 | 2 | V |
| | | $I_F = 10\text{ A}$; $T_j = 150\text{ °C}$; Fig. 6 | - | - | 1.6 | V |
| I_R | reverse current | $V_R = 600\text{ V}$; $T_j = 25\text{ °C}$ | - | - | 10 | μA |
| | | $V_R = 500\text{ V}$; $T_j = 150\text{ °C}$ | - | - | 250 | μA |
| Dynamic characteristics | | | | | | |
| Q_r | recovered charge | $I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 123 | - | nC |
| | | $I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7 | - | 305 | - | nC |
| t_{rr} | reverse recovery time | $I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $di_F/dt = 50\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 35 | 50 | ns |
| | | $I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 50 | - | ns |
| | | $I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7 | - | 78 | - | ns |
| | | $I_F = 10\text{ A}$; $V_R = 400\text{ V}$; $di_F/dt = 500\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 42 | - | ns |
| I_{RM} | peak reverse recovery current | $I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 4.9 | - | A |
| | | $I_F = 10\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7 | - | 7.8 | - | A |
| Avalanche energy | | | | | | |
| E_{AS} | non-repetitive avalanche energy | $I_R = 2.6\text{ A}$; $T_{j(\text{init})} = 25\text{ °C}$; $L = 15\text{ mH}$ | - | 50 | - | mJ |



$V_o = 1.268 \text{ V}; R_s = 0.031 \Omega$

- (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 6. Forward current as a function of forward voltage

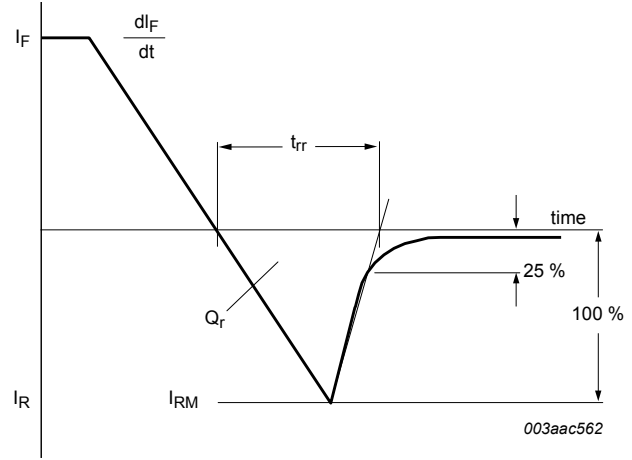
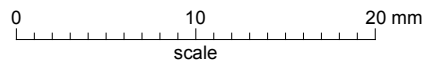
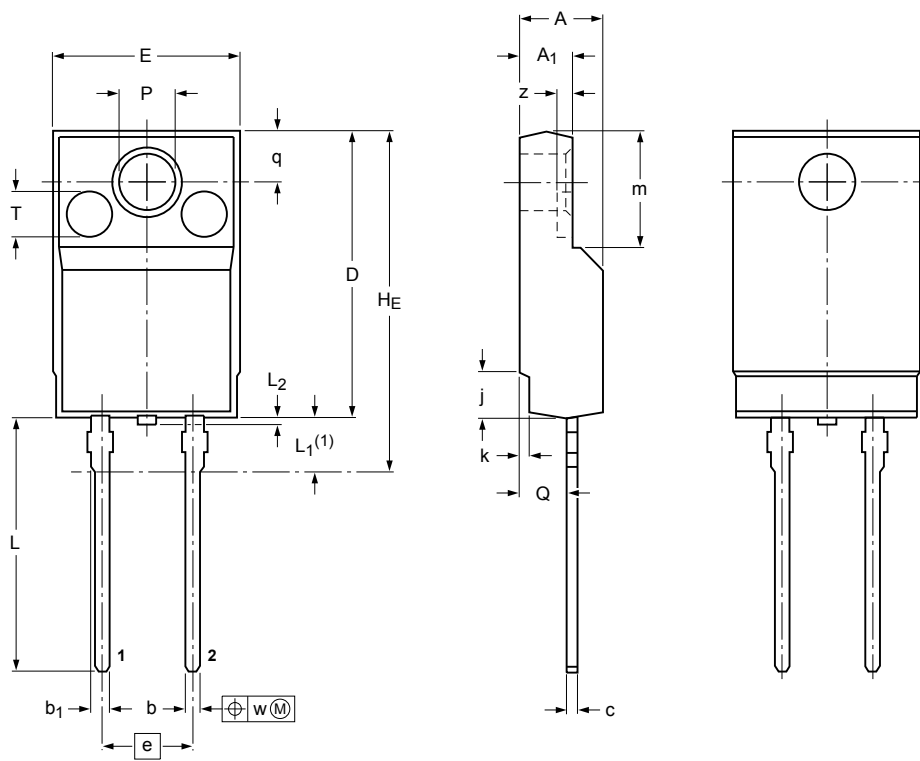


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 2-lead TO-220 'full pack'

SOD113



| |
|------------------|
| z ⁽²⁾ |
| 0.8 |

DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | b ₁ | c | D | E | e | H _E max | j | k | L | L ₁ ⁽¹⁾ | L ₂ max | m | P | Q | q | T | w |
|------|------------|----------------|------------|----------------|------------|--------------|-------------|------|-----------------------|------------|------------|--------------|-------------------------------|-----------------------|------------|------------|------------|-----|------|-----|
| mm | 4.6 4.0 | 2.9 2.5 | 0.9 0.7 | 1.1 0.9 | 0.7 0.4 | 15.8 15.2 | 10.3 9.7 | 5.08 | 19.0 | 2.7 1.7 | 0.6 0.4 | 14.4 13.5 | 3.3 2.8 | 0.5 | 6.5 6.3 | 3.2 3.0 | 2.6 2.3 | 2.6 | 2.55 | 0.4 |

Notes

- 1. Terminals are uncontrolled within zone L₁.
- 2. z is depth of T.

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|----------------|-------|------------------------|----------------------|
| | IEC | JEDEC | JEITA | | |
| SOD113 | | 2-lead TO-220F | | | 02-04-09 07-06-18 |

Fig. 8. Package outline TO-220F (SOD113)

12. Legal information

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|--------------------------------|--------------------|---|
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Date of release: 25 September 2014